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FIG. 1A

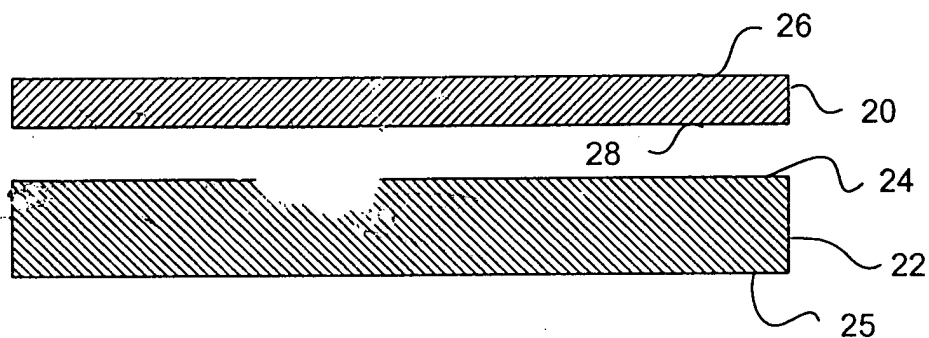


FIG. 1B

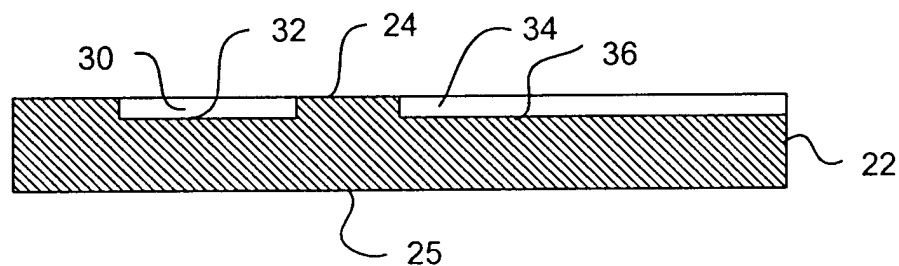


FIG. 1C

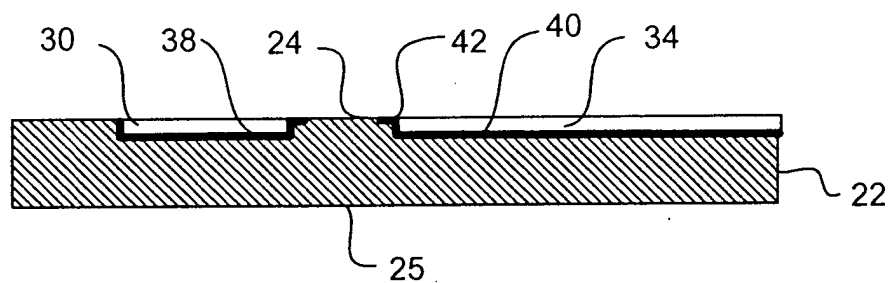


FIG. 1D

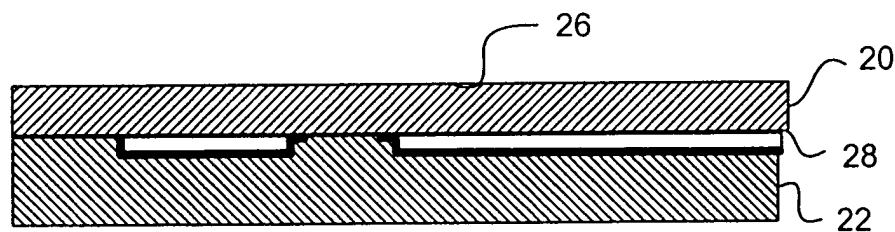


FIG. 1E

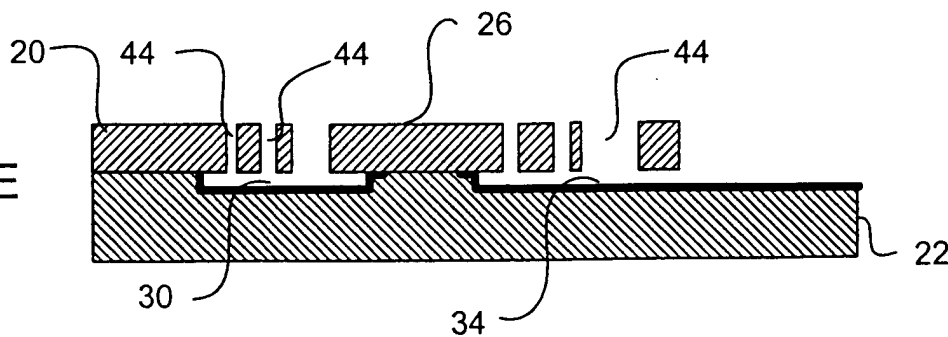


Figure 1 is a cross-sectional view of a semiconductor device. The device includes a substrate 22, a layer 24, and a layer 25. A patterned layer 26 is formed on top of layer 24, with openings 128 and 129. A layer 130 is formed between layer 24 and layer 25. A contact 128 is shown in the opening 128.



FIG. 3A

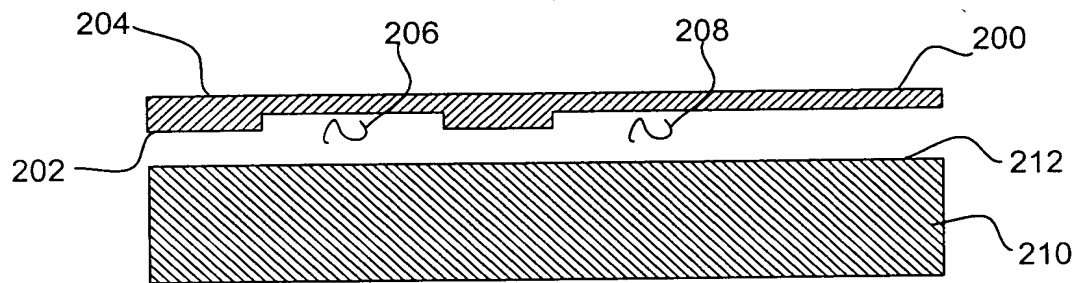


FIG. 3B

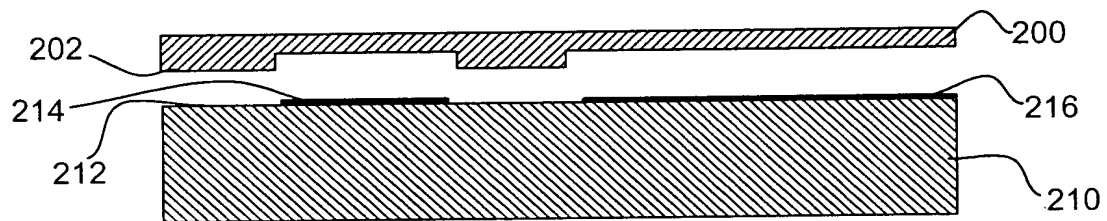


FIG. 3C

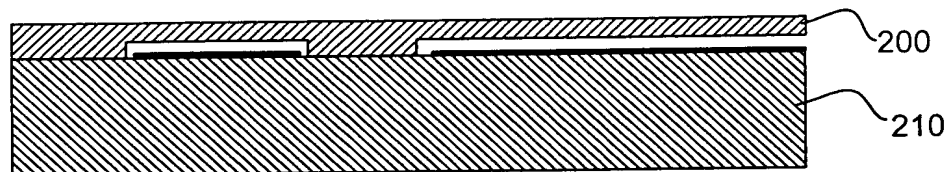


FIG. 4A

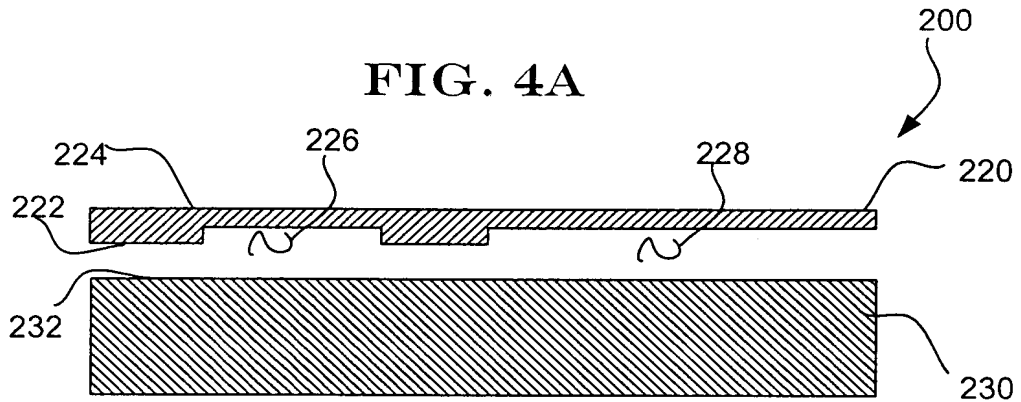


FIG. 4B

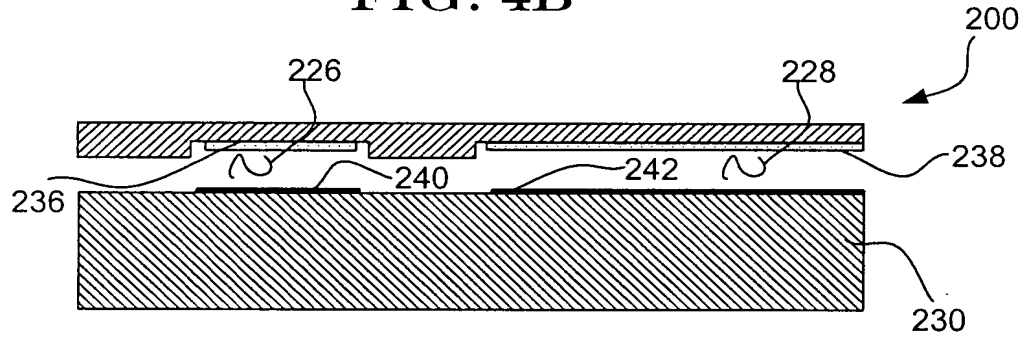


FIG. 4C

